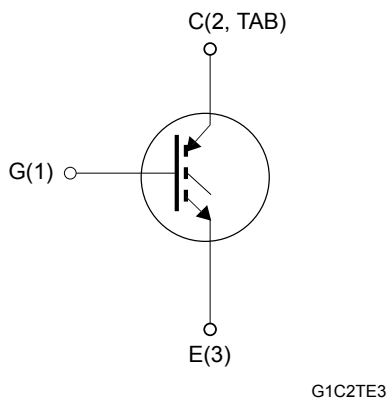
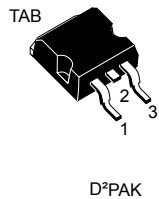


Trench gate field-stop IGBT, HB series 650 V, 40 A high speed



Features

- Maximum junction temperature: $T_J = 175\text{ °C}$
- High speed switching series
- Minimized tail current
- Low saturation voltage: $V_{CE(sat)} = 1.6\text{ V (typ.) @ } I_C = 40\text{ A}$
- Tight parameter distribution
- Safe paralleling
- Low thermal resistance

Applications

- Photovoltaic inverters
- High frequency converters

Description

This device is an IGBT developed using an advanced proprietary trench gate field-stop structure. The device is part of the new HB series of IGBTs, which represents an optimum compromise between conduction and switching loss to maximize the efficiency of any frequency converter. Furthermore, the slightly positive $V_{CE(sat)}$ temperature coefficient and very tight parameter distribution result in safer paralleling operation.

Product status link

[STGB40H65FB](#)

Product summary

Order code	STGB40H65FB
Marking	GB40H65FB
Package	D ² PAK
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage ($V_{GE} = 0$ V)	650	V
I_C	Continuous collector current at $T_C = 25$ °C	80	A
	Continuous collector current at $T_C = 100$ °C	40	
$I_{CP}^{(1)}$	Pulsed collector current	160	A
V_{GE}	Gate-emitter voltage	± 20	V
P_{TOT}	Total power dissipation at $T_C = 25$ °C	283	W
T_{STG}	Storage temperature range	- 55 to 150	°C
T_J	Operating junction temperature range	- 55 to 175	

1. Pulse width limited by maximum junction temperature.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case	0.53	°C/W
R_{thJA}	Thermal resistance junction-ambient	62.5	

2 Electrical characteristics

$T_C = 25\text{ °C}$ unless otherwise specified

Table 3. Static characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	$V_{GE} = 0\text{ V}$, $I_C = 2\text{ mA}$	650			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}$, $I_C = 40\text{ A}$		1.6	2	V
		$V_{GE} = 15\text{ V}$, $I_C = 40\text{ A}$, $T_J = 125\text{ °C}$		1.7		
		$V_{GE} = 15\text{ V}$, $I_C = 40\text{ A}$, $T_J = 175\text{ °C}$		1.8		
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 1\text{ mA}$	5	6	7	V
I_{CES}	Collector cut-off current	$V_{GE} = 0\text{ V}$, $V_{CE} = 650\text{ V}$			25	μA
I_{GES}	Gate-emitter leakage current	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			± 250	nA

Table 4. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0\text{ V}$	-	5412	-	μF
C_{oes}	Output capacitance		-	198	-	
C_{res}	Reverse transfer capacitance		-	107	-	
Q_g	Total gate charge	$V_{CC} = 520\text{ V}$, $I_C = 40\text{ A}$, $V_{GE} = 0\text{ to }15\text{ V}$ (see Figure 22. Gate charge test circuit)	-	210	-	nC
Q_{ge}	Gate-emitter charge		-	39	-	
Q_{gc}	Gate-collector charge		-	82	-	

Table 5. Switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400\text{ V}$, $I_C = 40\text{ A}$, $V_{GE} = 15\text{ V}$, $R_G = 5\ \Omega$ (see Figure 21. Test circuit for inductive load switching)	-	40	-	ns
t_r	Current rise time		-	13	-	
$(di/dt)_{on}$	Turn-on current slope		-	2413	-	A/ μ s
$t_{d(off)}$	Turn-off-delay time		-	142	-	ns
t_f	Current fall time		-	27	-	
$E_{on}^{(1)}$	Turn-on switching energy		-	498	-	μ J
$E_{off}^{(2)}$	Turn-off switching energy		-	363	-	
E_{ts}	Total switching energy		-	861	-	
$t_{d(on)}$	Turn-on delay time		$V_{CE} = 400\text{ V}$, $I_C = 40\text{ A}$, $V_{GE} = 15\text{ V}$, $R_G = 5\ \Omega$, $T_J = 175\text{ }^\circ\text{C}$ (see Figure 21. Test circuit for inductive load switching)	-	38	-
t_r	Current rise time	-		14	-	
$(di/dt)_{on}$	Turn-on current slope	-		2186	-	A/ μ s
$t_{d(off)}$	Turn-off-delay time	-		141	-	ns
t_f	Current fall time	-		61	-	
$E_{on}^{(1)}$	Turn-on switching energy	-		1417	-	μ J
$E_{off}^{(2)}$	Turn-off switching energy	-		764	-	
E_{ts}	Total switching energy	-		2181	-	

1. Including the reverse recovery of the external diode.
2. Including the tail of the collector current.

2.1 Electrical characteristics (curves)

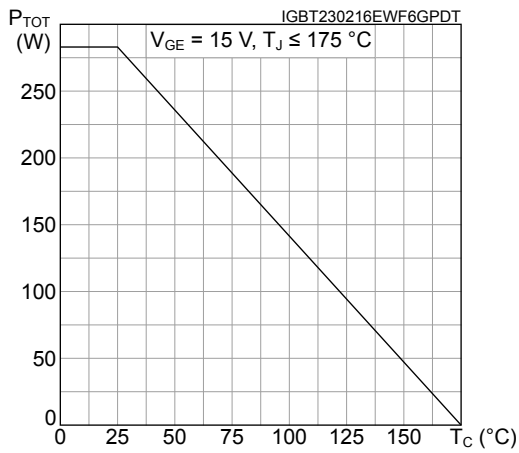
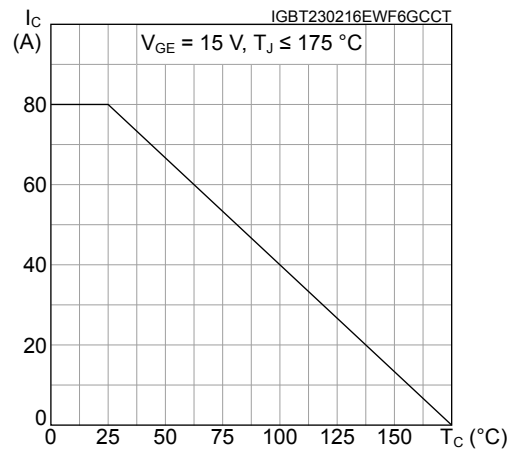
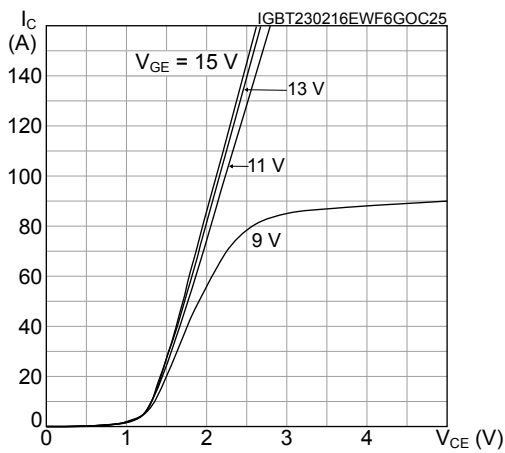
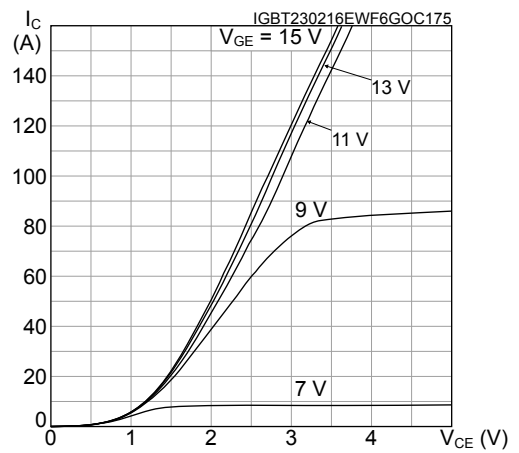
Figure 1. Power dissipation vs. case temperature

Figure 2. Collector current vs. case temperature

Figure 3. Output characteristics ($T_J = 25 \text{ }^\circ\text{C}$)

Figure 4. Output characteristics ($T_J = 175 \text{ }^\circ\text{C}$)


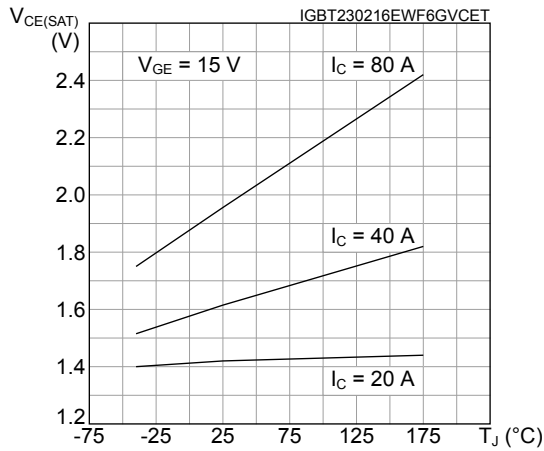
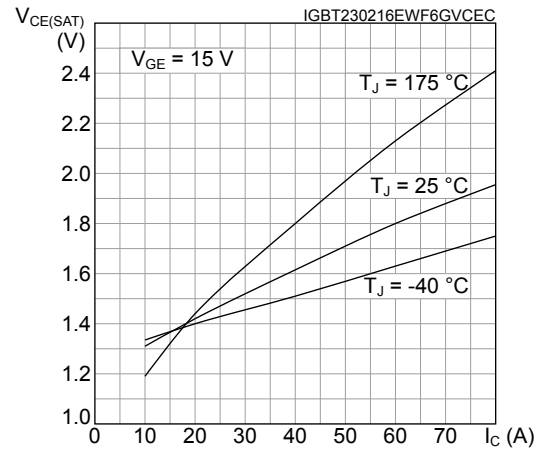
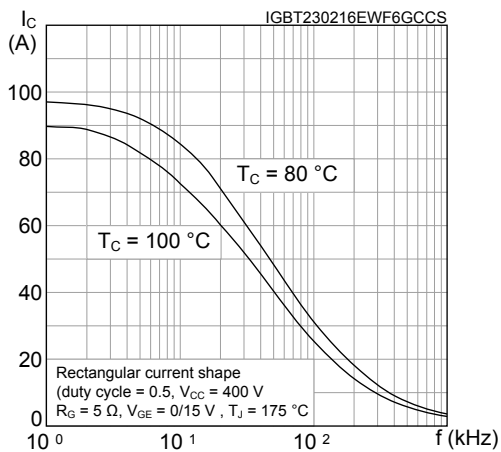
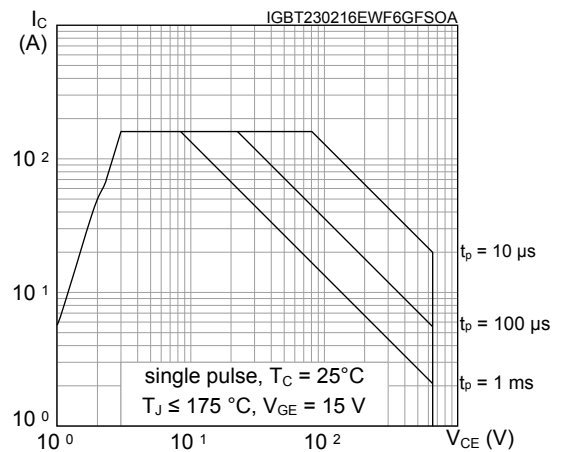
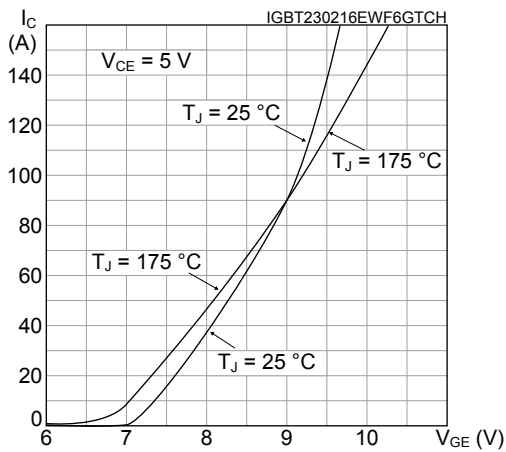
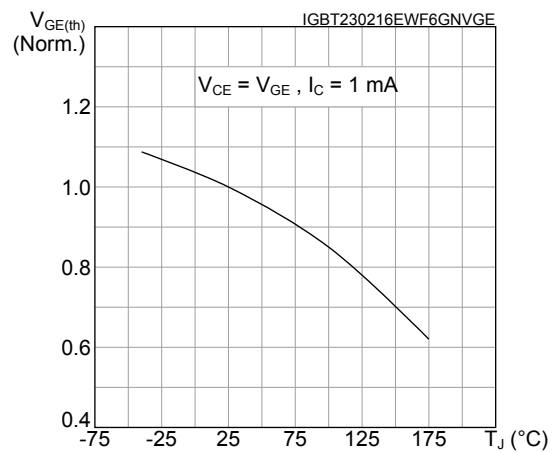
Figure 5. $V_{CE(sat)}$ vs. junction temperature

Figure 6. $V_{CE(sat)}$ vs. collector current

Figure 7. Collector current vs. switching frequency

Figure 8. Forward bias safe operating area

Figure 9. Transfer characteristics

Figure 10. Normalized $V_{GE(th)}$ vs. junction temperature


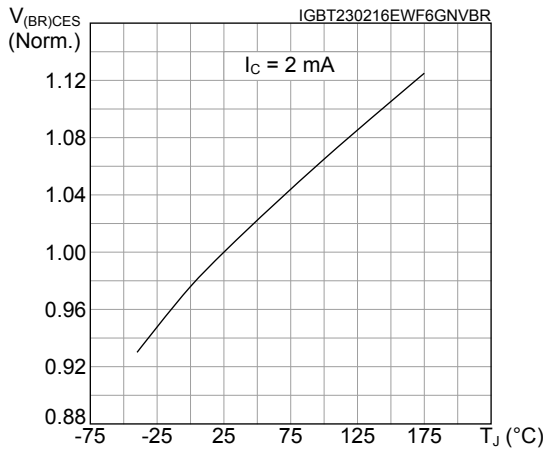
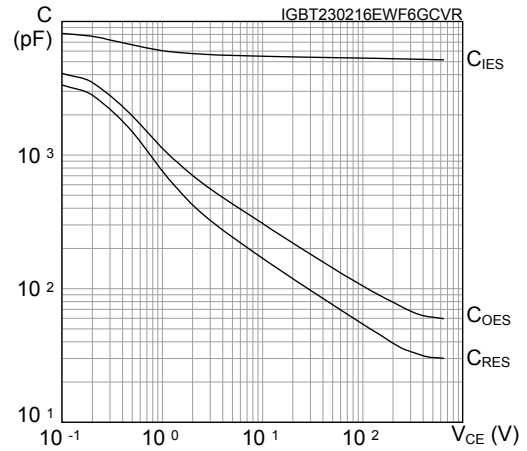
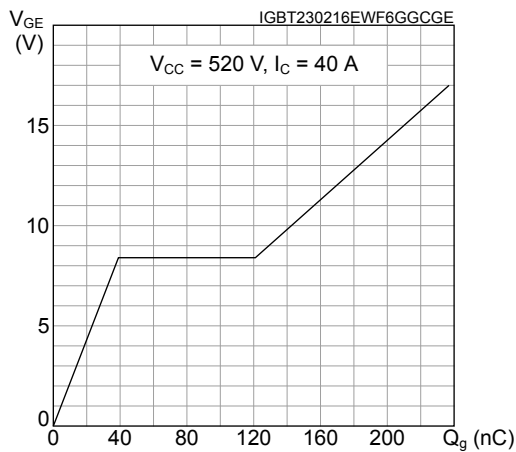
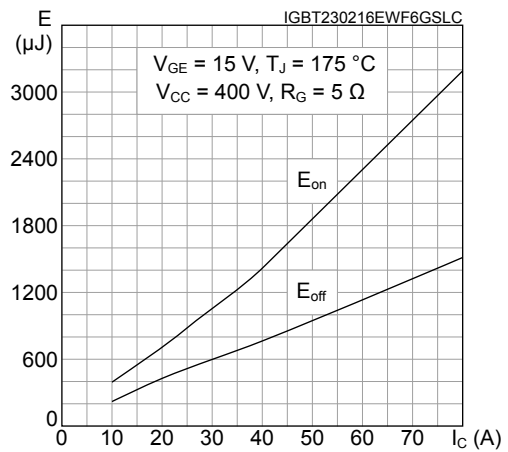
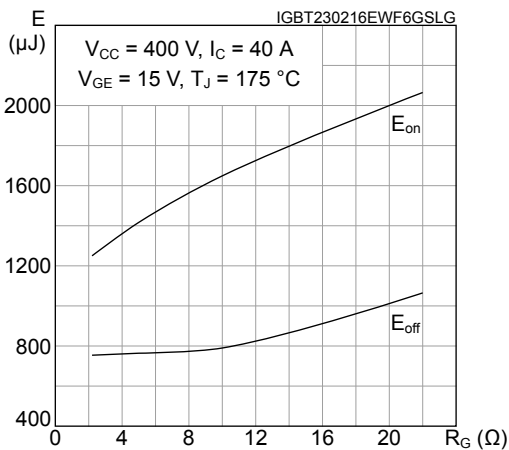
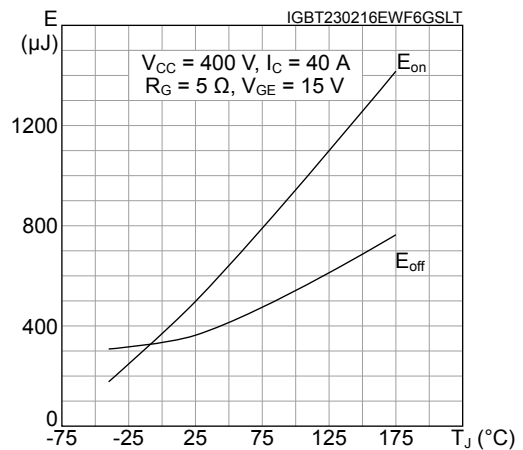
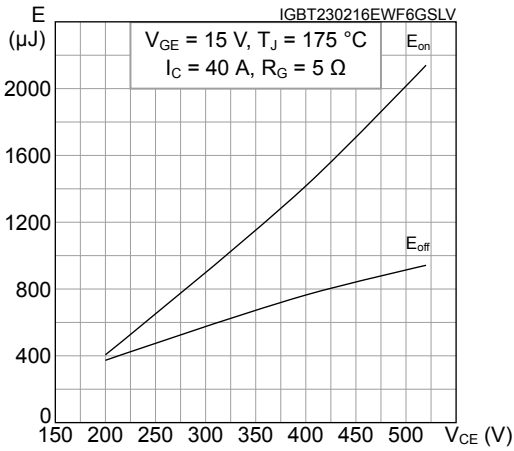
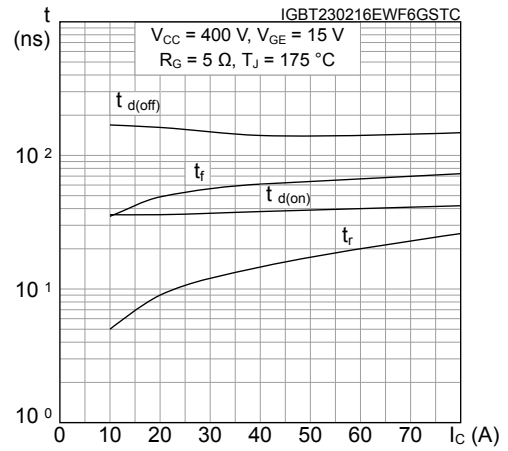
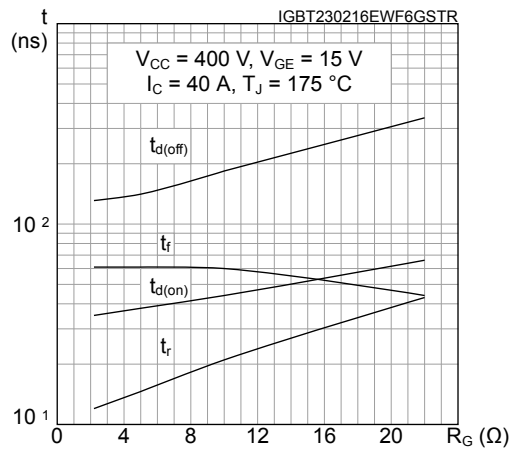
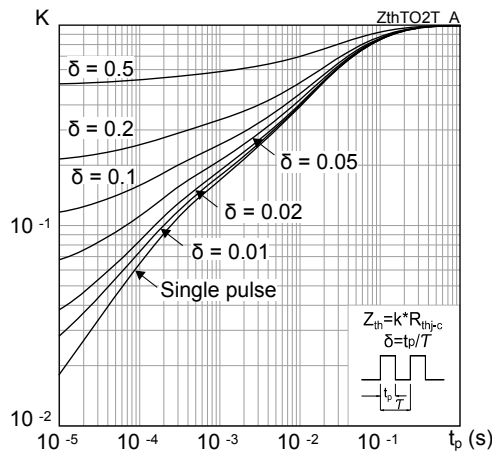
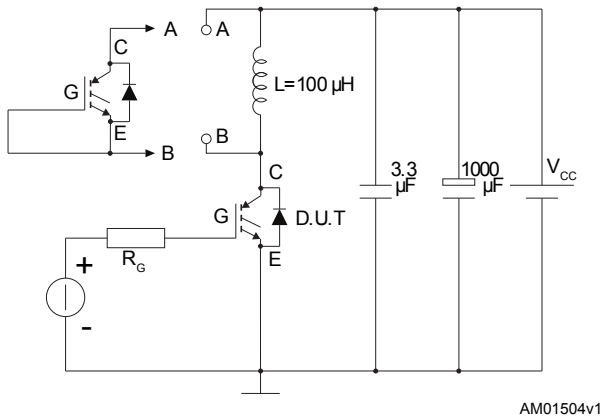
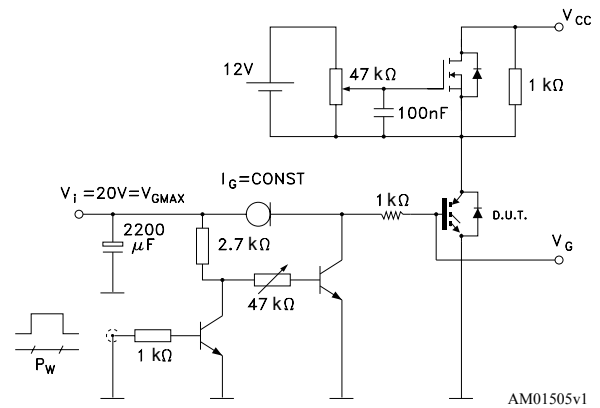
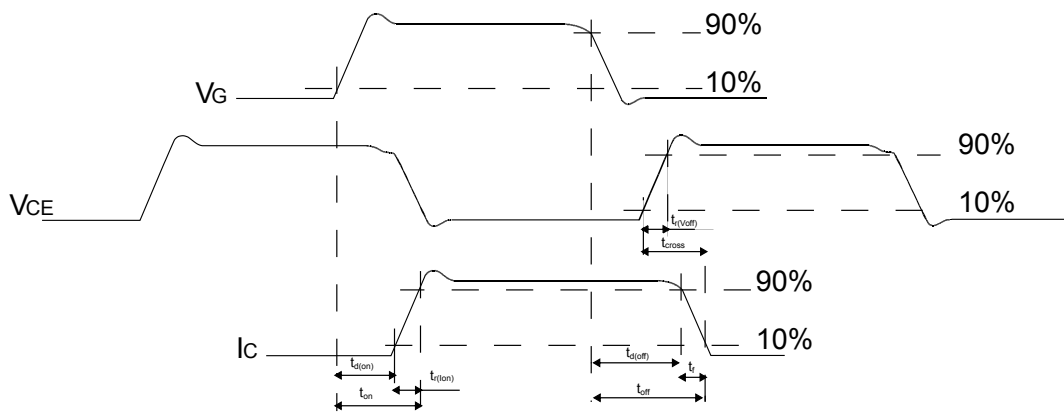
Figure 11. Normalized $V_{(BR)CES}$ vs. junction temperature

Figure 12. Capacitance variations

Figure 13. Gate charge vs. gate-emitter voltage

Figure 14. Switching energy vs. collector current

Figure 15. Switching energy vs. gate resistance

Figure 16. Switching energy vs. temperature


Figure 17. Switching energy vs. collector emitter voltage

Figure 18. Switching times vs. collector current

Figure 19. Switching times vs. gate resistance

Figure 20. Thermal impedance


3 Test circuits

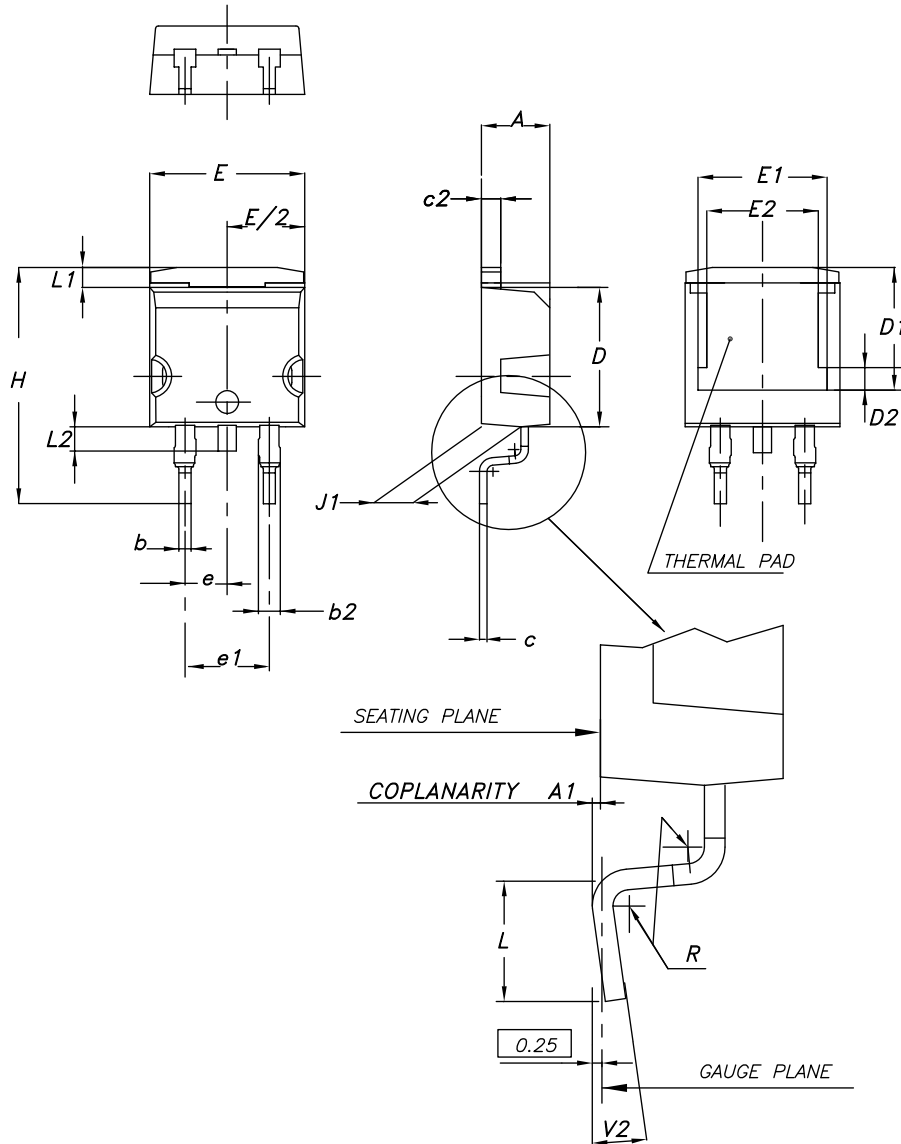
Figure 21. Test circuit for inductive load switching

Figure 22. Gate charge test circuit

Figure 23. Switching waveform


4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK®** packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 D²PAK (TO-263) type A2 package information

Figure 24. D²PAK (TO-263) type A2 package outline

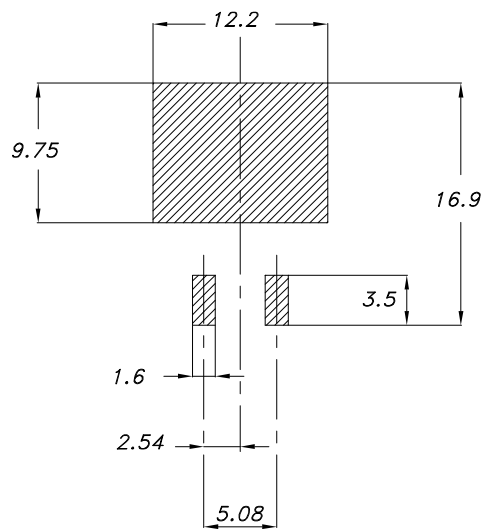


0079457_A2_25

Table 6. D²PAK (TO-263) type A2 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10.00		10.40
E1	8.70	8.90	9.10
E2	7.30	7.50	7.70
e		2.54	
e1	4.88		5.28
H	15.00		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.40	
V2	0°		8°

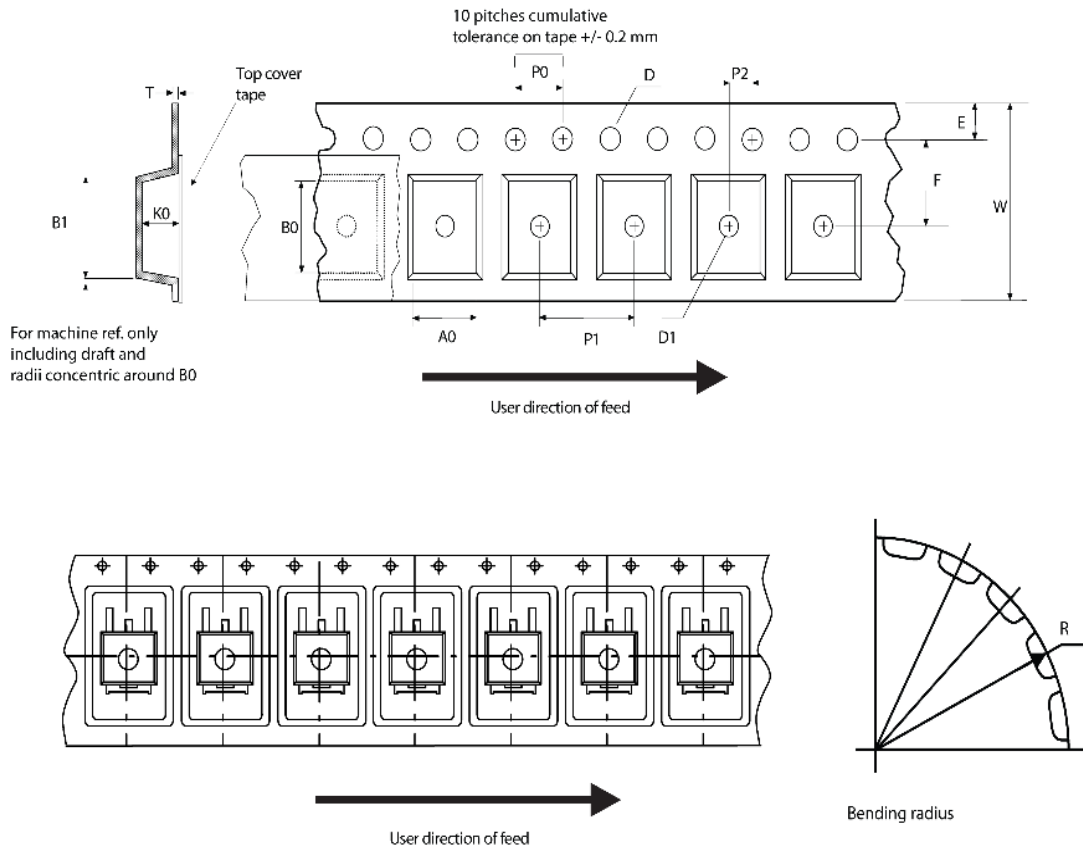
Figure 25. D²PAK (TO-263) recommended footprint (dimensions are in mm)



Footprint

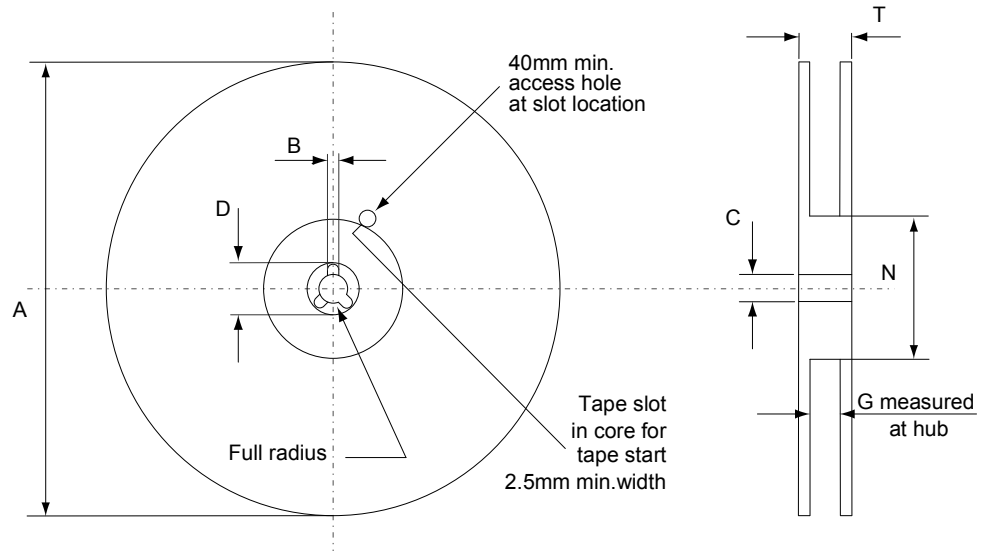
4.2 D²PAK packing information

Figure 26. D²PAK tape outline



AM08852v1

Figure 27. D²PAK reel outline



AM06038v1

Table 7. D²PAK tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Revision history

Table 8. Document revision history

Date	Revision	Changes
27-Jun-2016	1	Initial release.
13-Feb-2019	2	Updated Section 4.1 D²PAK (TO-263) type A2 package information.

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